

Features

- Trench Power LV MOSFET Technology
- Excellent Package for Heat Dissipation
- High Density Cell Design for Low $R_{DS(ON)}$
- Halogen Free. "Green" Device (Note 1)
- Epoxy Meets UL 94 V-0 Flammability Rating
- Lead Free Finish/RoHS Compliant ("P" Suffix Designates RoHS Compliant. See Ordering Information)
- Moisture Sensitivity Level 1

Maximum Ratings

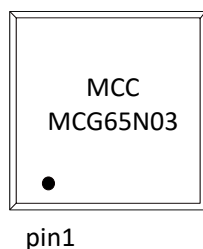
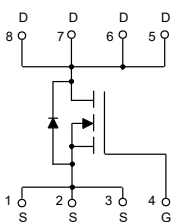
- Operating Junction Temperature Range : -55°C to +150°C
- Storage Temperature Range: -55°C to +150°C
- Thermal Resistance: 20°C/W Junction to Ambient⁽²⁾
- Thermal Resistance: 7.1°C/W Junction to Case

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	±20	V
Continuous Drain Current	I_D	$T_C=25^\circ\text{C}$	65
		$T_A=25^\circ\text{C}$	40
		$T_A=70^\circ\text{C}$	32
Pulsed Drain Current ⁽³⁾	I_{DM}	240	A
Total Power Dissipation ⁽⁴⁾	P_D	75	W
Single Pulsed Avalanche Energy ⁽⁵⁾	E_{AS}	400	mJ

Note:

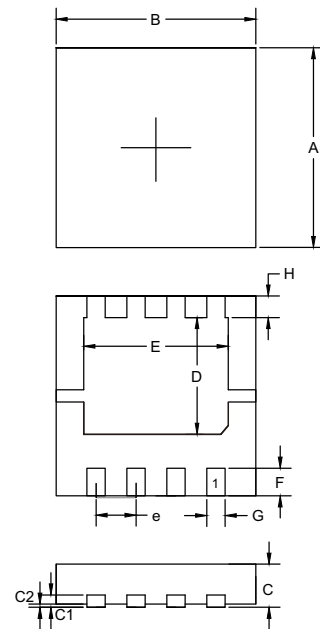
1. Halogen free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
2. The value of $R_{\theta JA}$ is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^\circ\text{C}$.
3. Pulse Test: Pulse Width ≤ 300us, Duty cycle ≤ 2%.
4. The power dissipation P_D is based on $T_{J(MAX)}=150^\circ\text{C}$, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.
5. $T_J=25^\circ\text{C}$, $V_{DD}=20\text{V}$, $V_G=10\text{V}$, $L=2.0\text{mH}$, $R_g=25\Omega$.

Internal Structure and Marking Code



N-CHANNEL MOSFET

DFN3333



DIM	DIMENSIONS				NOTE
	INCHES		MM		
	MIN	MAX	MIN	MAX	
A	0.126	0.130	3.20	3.30	
B	0.126	0.130	3.20	3.30	
C	0.030	0.033	0.75	0.85	
C1	0.007	0.009	0.18	0.22	
C2	---	0.002	---	0.05	
D	0.071	0.079	1.80	2.00	
E	0.087	0.098	2.20	2.50	
F	0.016	0.020	0.40	0.50	
G	0.010	0.014	0.25	0.35	
H	0.012	0.016	0.30	0.40	
e	0.024	0.028	0.60	0.70	

Electrical Characteristics @ 25°C (Unless Otherwise Specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS}=0V, I_D=250\mu A$	30			V
Gate-Source Leakage Current	I_{GSS}	$V_{DS}=0V, V_{GS}=\pm 20V$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=30V, V_{GS}=0V$			1	μA
Gate-Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	1	1.5	2.5	V
Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=20A$		2.6	3.2	m Ω
		$V_{GS}=4.5V, I_D=20A$		3.4	4	m Ω
Gate Resistance	R_g	F=1 MHz, Open drain		2.9		Ω
Diode Characteristics						
Continuous Body Diode Current	I_S				65	A
Diode Forward Voltage	V_{SD}	$V_{GS}=0V, I_S=20A$			1.2	V
Reverse Recovery Time	t_{rr}	$I_F=20A, di_F/dt=500A/\mu s$		15		ns
Reverse Recovery Charge	Q_{rr}			3		nC
Dynamic Characteristics						
Input Capacitance	C_{iss}	$V_{DS}=15V, V_{GS}=0V, f=1MHz$		4498		pF
Output Capacitance	C_{oss}			800		
Reverse Transfer Capacitance	C_{riss}			643		
Total Gate Charge	Q_g	$V_{DS}=15V, V_{GS}=10V, I_D=20A$		92.7		nC
Gate-Source Charge	Q_{gs}			13.5		
Gate-Drain Charge	Q_{gd}			22.8		
Turn-On Delay Time	$t_{d(on)}$	$V_{DS}=20V, V_{GS}=10V,$ $R_G=3\Omega, R_L=0.75\Omega,$ $I_{DS}=4A$		11		ns
Turn-On Rise Time	t_r			80		
Turn-Off Delay Time	$t_{d(off)}$			39		
Turn-Off Fall Time	t_f			92		

Curve Characteristics

Fig. 1 - Typical Output Characteristics

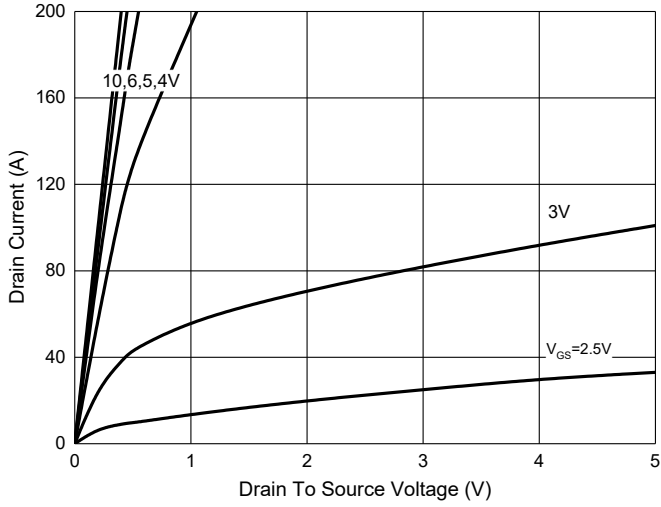


Fig. 2 - Transfer Characteristics

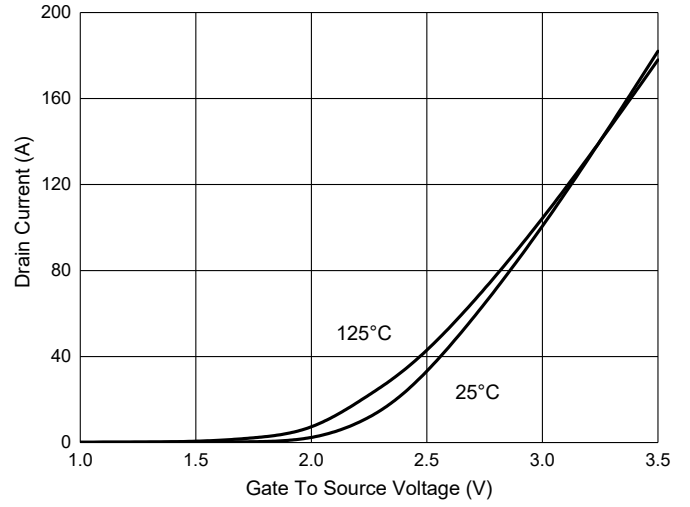


Fig. 3 - $R_{DS(ON)} - I_D$

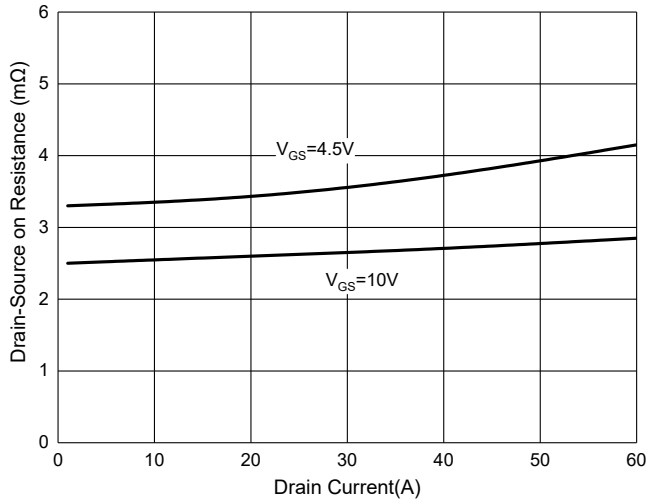


Fig. 4 - Normalized On Resistance Characteristics

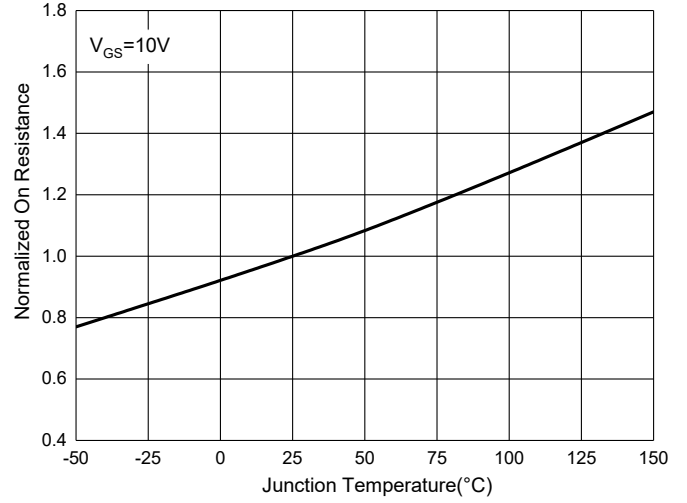


Fig. 5 - Capacitance Characteristics

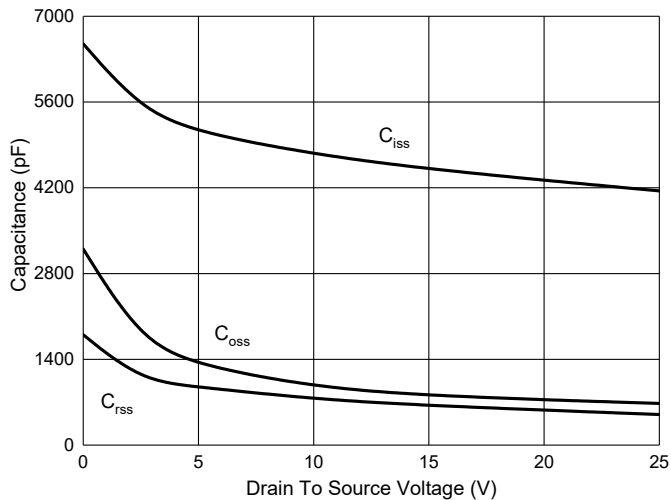
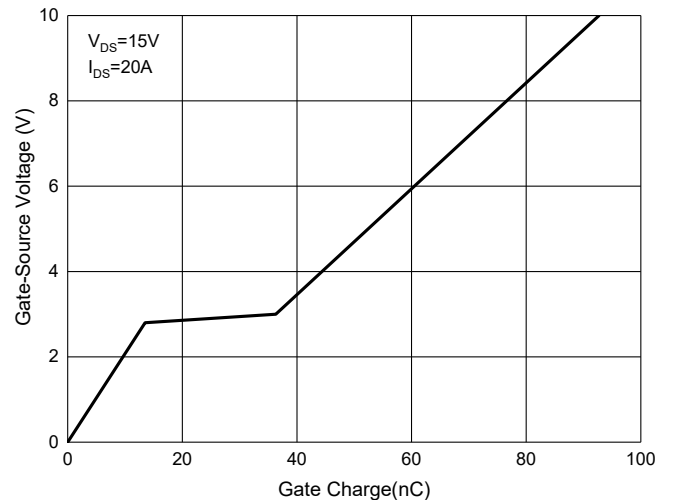


Fig. 6 - Gate Charge



Curve Characteristics

Fig. 7 - Safe Operation Area

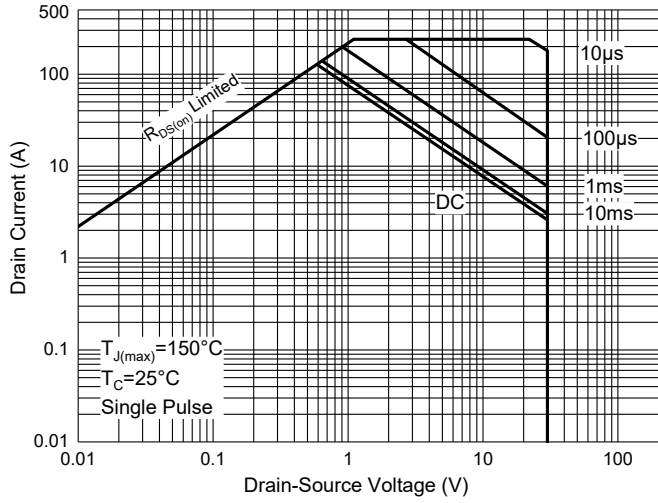
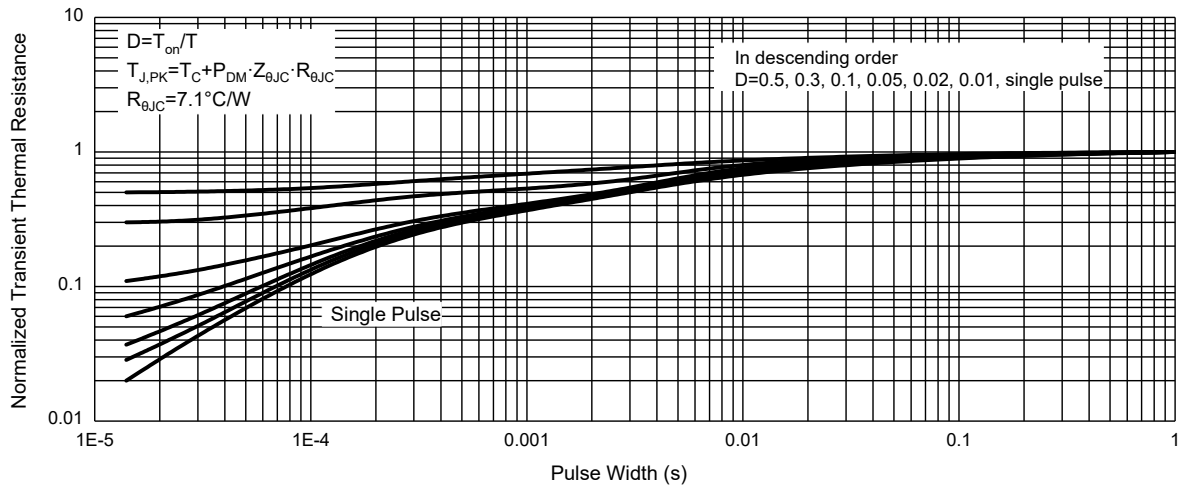


Fig. 8 - Normalized Transient Thermal Impedance



Ordering Information

Device	Packing
Part Number-TP	Tape&Reel: 5Kpcs/Reel

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